

List of Publications

Monographs:

1. P.Rudolph, Profilzüchtung von Einkristallen (in German), [Trans: The Shaped Crystal Growth], Akademie Verlag Berlin 1982.
2. P.Rudolph, 4 chapters in: K.-Th-Wilke, J.Bohm, Kristallzüchtung (in German), Unter Mitwirkung von P. Görnert, M. Jurisch, M. Ritschel, P. Rudolph und W. Schröder [Trans: Crystal Growth], Deutscher Verlag der Wiss. Berlin 1988 und H. Deutsch and Thun, Frankfurt a.M. 1988.

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12. P. Rudolph, Elements of Thermodynamics for the Understanding and Design of Crystal Growth Processes, in: R. Fornari, C. Paorici (eds.), Theoretical and Technological Aspects of Crystal Growth (Trans Tech Publications, Switzerland 1998) 1-26.
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14. P. Rudolph, Theoretical Concepts of Crystal Growth (Thermodynamics and Kinetics) in: R. Fornari and L. Sorba (eds.), Crystal Growth of Materials for Energy Production and Energy-saving Applications (Edizioni ETS, Pisa 2001) 7-26.
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19. P. Rudolph, What do we want with fiber crystals – an introductory review, in: T. Fukuda, P. Rudolph, S. Uda (eds.), Fiber Crystal Growth from the Melt, Ser. Adv. in Materials Res. 6 (Springer, Berlin 2004) p.1 - 46.
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The Horizontal Bridgman Method.
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